

**AMENDMENTS TO THE CLAIMS**

Applicants submit below a complete listing of the current claims, including marked-up claims with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing. This listing of claims replaces all prior versions, and listings, of claims in the application:

**Listing of the Claims**

1. (Currently amended) An integrated circuit comprising one or several metallization levels, metal conductive strips and metal contact pads being formed on a last metallization level, wherein the metal contact pads have a first length, a first width, and a first thickness, the first thickness being the distance from a bottom of the metal contact pads to a top of the metal contact pads, wherein the first length and the first width are greater than the first thickness, the last level being covered with a passivation layer in which are formed openings above the contact pads, wherein the metal conductive strips have a second thickness along a same direction as the first thickness, wherein an entire the first thickness of the metal contact pads, at least at a level of their for portions of the metal contact pads that are not covered by the passivation layer, is smaller than the second thickness of said conductive strips, wherein the second thickness is at least twice as large as the first thickness.
2. (Original) The integrated circuit of claim 1, wherein at least one conductive strip forms a coil.
3. (Original) The integrated circuit of claim 1, wherein several of said conductive strips form a supply network.
4. (Original) The integrated circuit of claim 1, wherein the last metallization level is formed on an insulating layer, each contact pad being formed of a conductive layer covering an insulating portion laid on the insulating layer.
5. (Original) The integrated circuit of claim 1, wherein the contact pads are made of

aluminum.

6. (Original) A method for forming the last metallization level of the integrated circuit of claim 1, comprising:

depositing a metal layer on a substrate;

etching the metal layer to form metal portions and said conductive strips;

covering the substrate, the conductive strips, and the metal portions with a passivation layer;

forming openings in the passivation layer above the metal portions; and

partially etching the metal portions to decrease their thickness to obtain said contact pads.

7. (Original) A method for forming the last metallization level of the integrated circuit of claim 1, comprising:

depositing a metal layer on a substrate;

etching the metal layer to form metal portions and said conductive strips;

covering the conductive strips with a protection layer;

partially etching the metal portions to decrease their thickness to obtain said contact pads;

removing, if necessary, the protection layer;

covering the substrate, the conductive strips, and the contact pads with a passivation layer; and

forming openings in the passivation layer above the contact pads.